

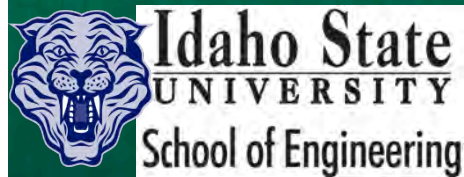


# IEEE SW Test Workshop

Semiconductor Wafer Test Workshop

June 9 - 12, 2013 | San Diego, California

## Study of Cantilever Probes and Probe Marks

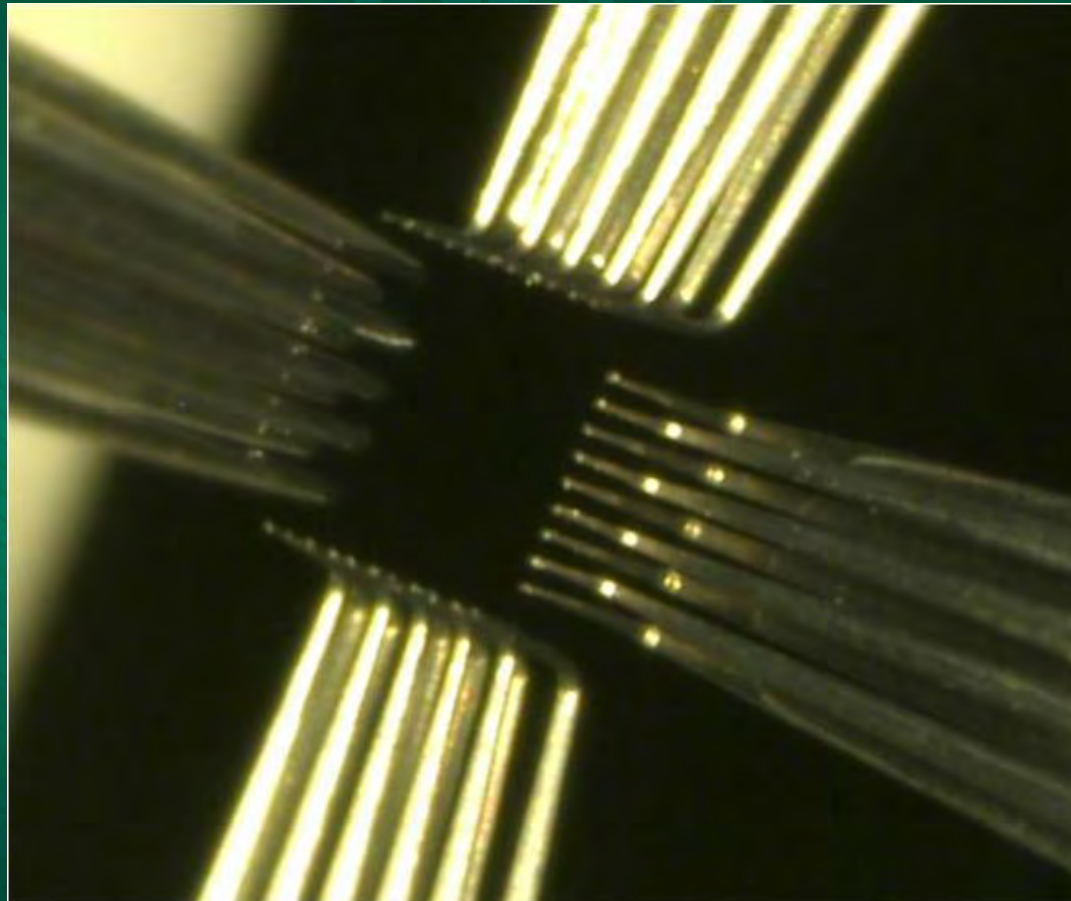


Stevan Hunter PhD<sup>1,2</sup>, Clint Churchill<sup>1</sup>,  
Vail McBride<sup>1</sup>, Tiago Rodrigues<sup>3</sup>,

Shashi Sharma<sup>3</sup>, Prakash Subedi<sup>3</sup>,  
Ruben Torres<sup>1,2</sup>, Dustin Whittaker<sup>3</sup>

<sup>1</sup>ON Semiconductor, <sup>2</sup>Idaho State University,  
<sup>3</sup>Brigham Young University Idaho

# Example Cantilever Probe Tips



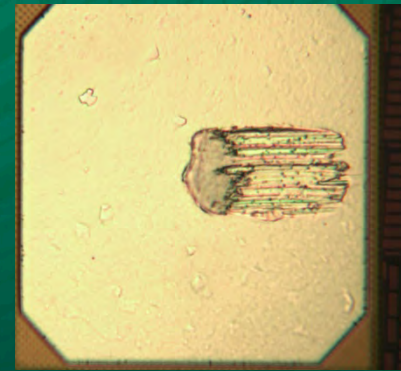
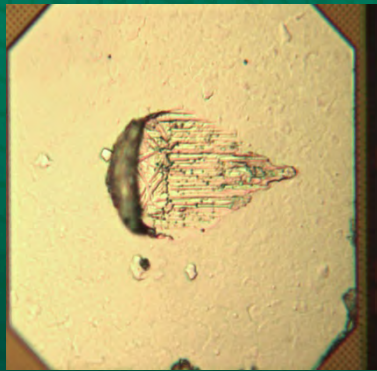
# Background

- **ASICs often require multiple probings**
- **Driven to lower cost while increasing reliability**
  - Pad structure mechanical robustness was improved
    - Thin pad Al
    - Circuit Under Pad on Al-SiO<sub>2</sub> CMOS technologies
    - Cu wire (instead of Au), ball bond or wedge bond
    - Shrinking pad size
- **Desire to continue to use inexpensive cantilever probe cards...**



# Probe Mark Examples

- Probe marks can have many different characteristics
- The marks below are from different probe tips, all at 4mils overdrive



# Objectives

- **Discover the best methods for using cantilever probe cards in volume ASIC production**
  - Bond pads are fragile (don't crack them)
  - Probe marks interfere with wirebond reliability
  - Robust tip performance and long lifetime desired
- **Probe mark requirements are tightening:**
  - small size
  - well positioned
  - non-invasive



# Experimental

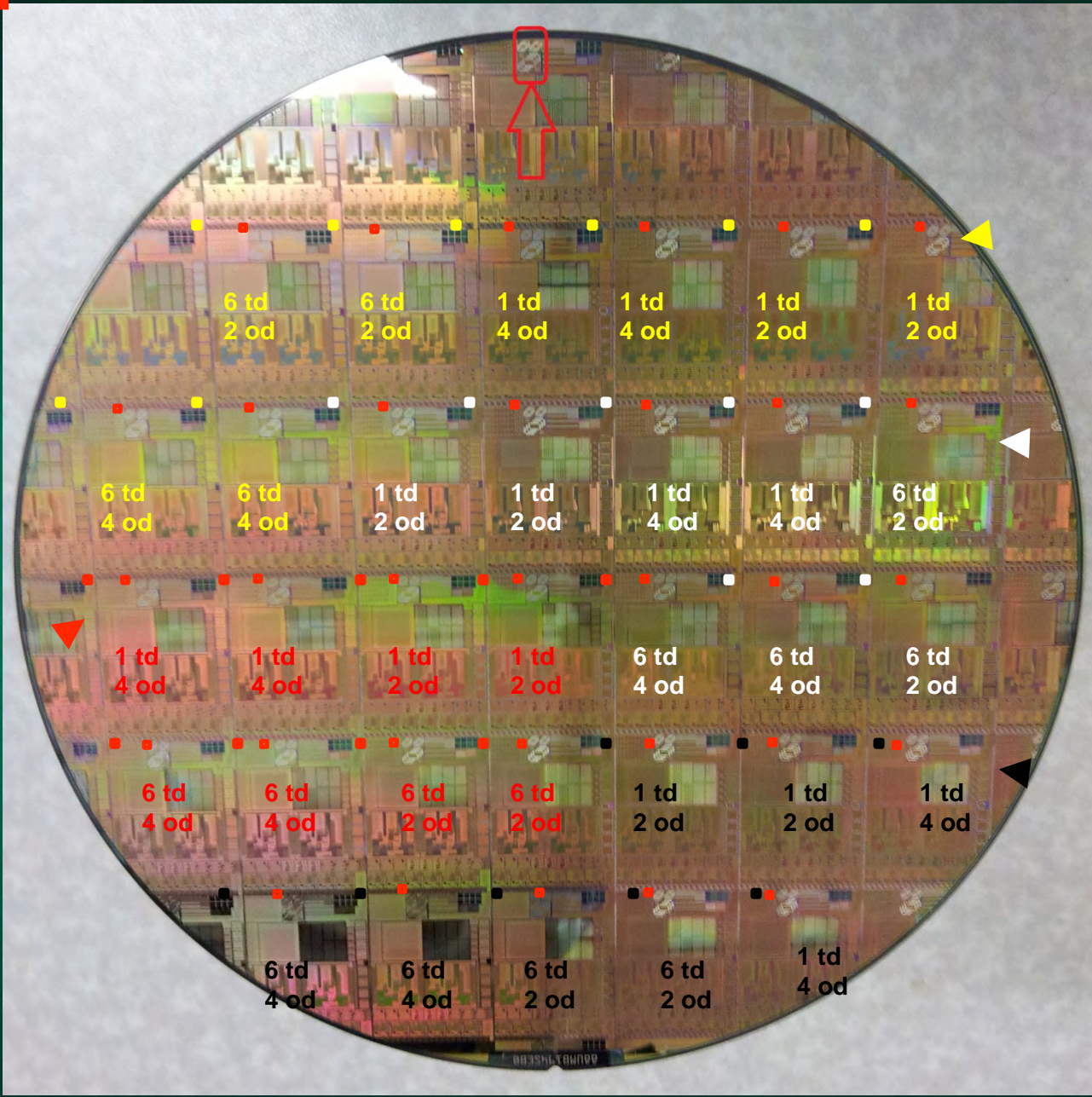
- **4 probe cards with W-Rh3% cantilever tips**
    - Four different probe cards, 40 tips, 2 tip lengths
    - 0.8mil, 1.0mil, 1.2mil tip diameters
    - 90°, 95°, 104° tip angles
  - **1 touchdown, 2 or 4mils overdrive**
  - **16 different bond pad structures**
  - **32 die probed in each treatment**
    - 40 pads per die
- **Probe marks analyzed for length, width, area**



# Cantilever Probe Cards Detail

Card Name	Tip Force	Tip Lengths	Tip Angle	Tip Diameter	# Die	2mil od	4mil od
A	High	Short, Long	104°	1mil	4	x	x
B	High	Short, Long	104°	0.8mil	4	x	x
C	High	Short, Long	100°	1mil	4	x	x
D	Med	Short, Long	90°, 95°, 104°	0.8, 1.0, 1.2mil	4	x	x





Probe Card "C"

Probe Card "A"

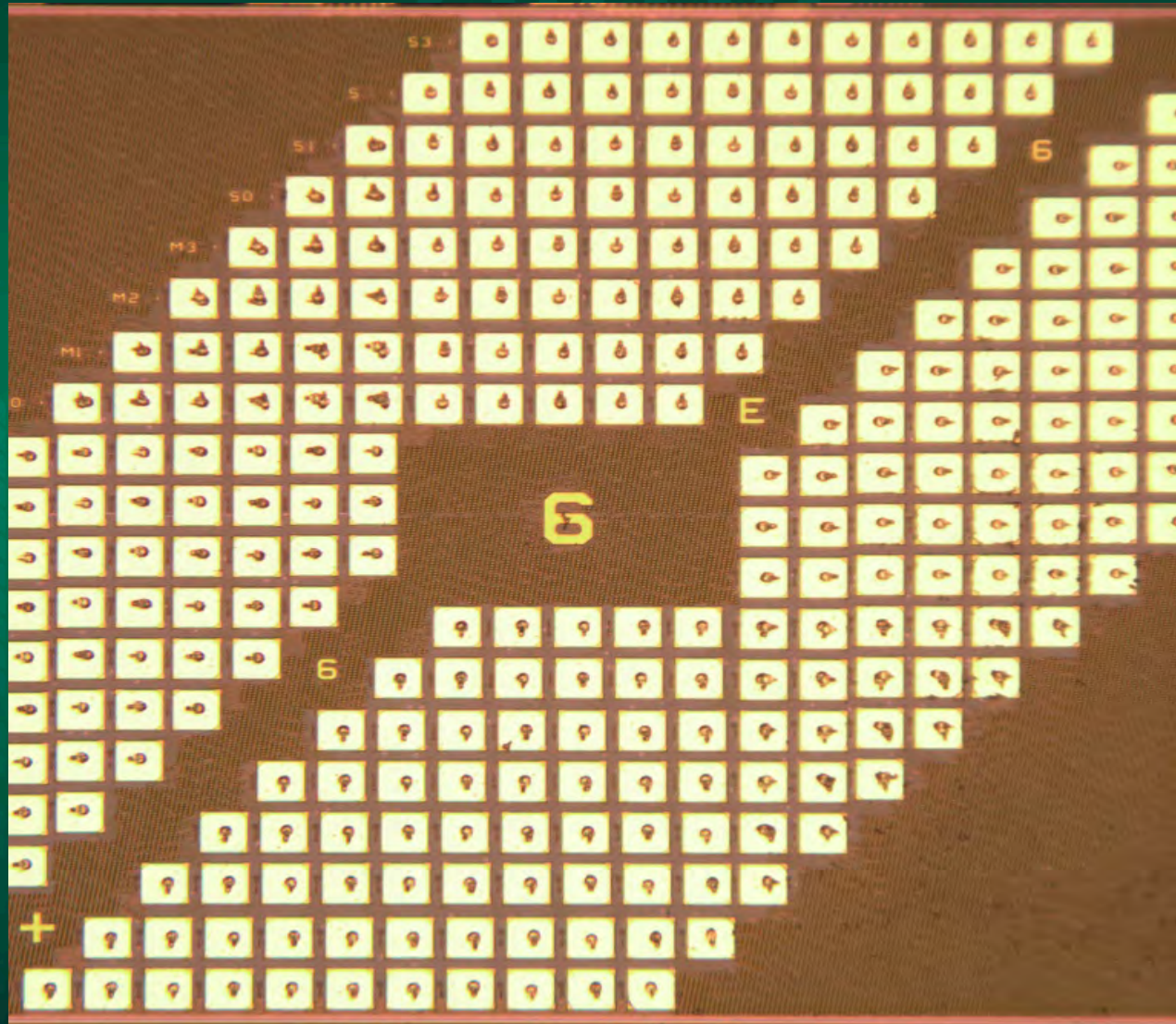
Probe Card "D"

Probe Card "B"

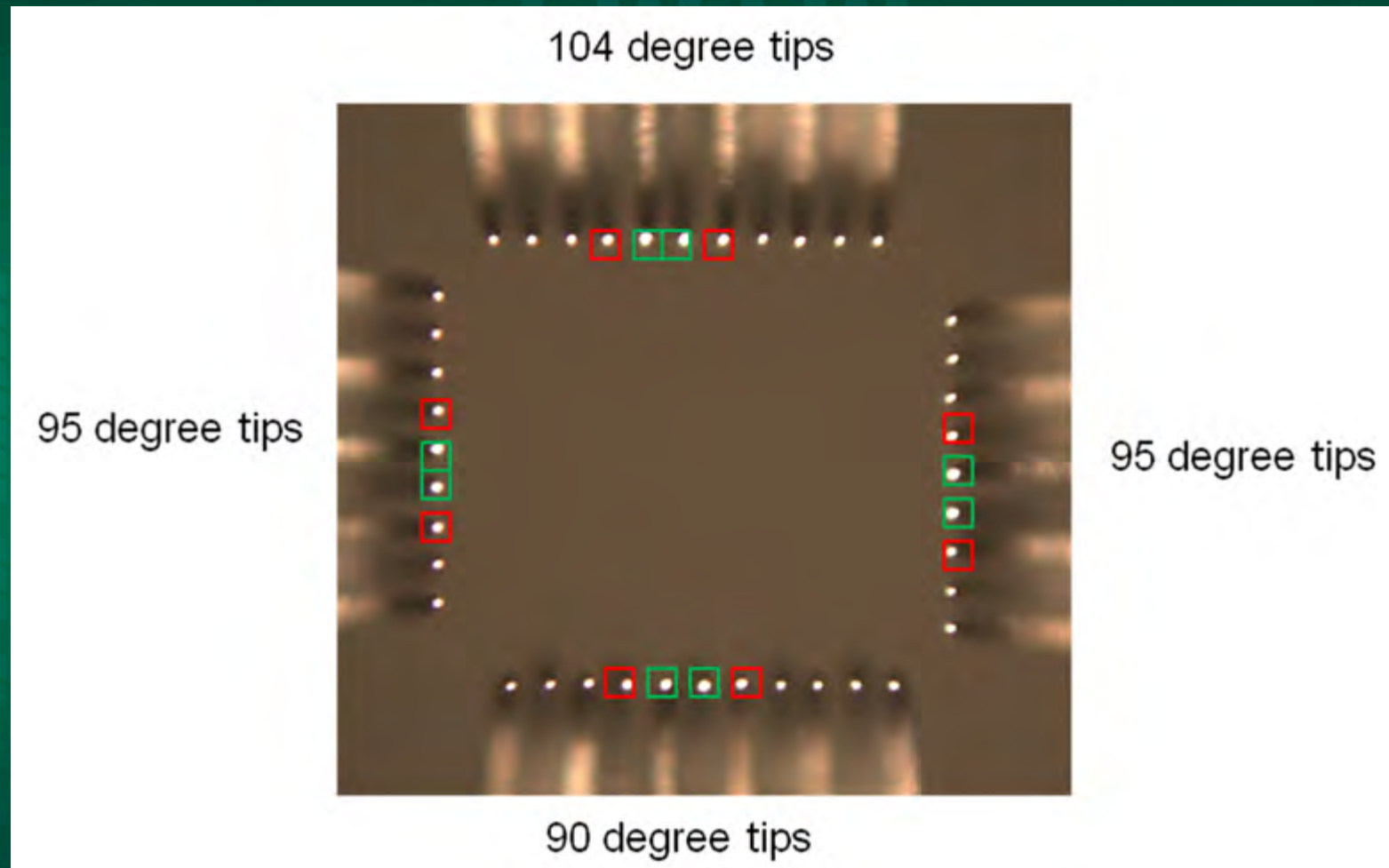




# Bond Pads Test Array Example

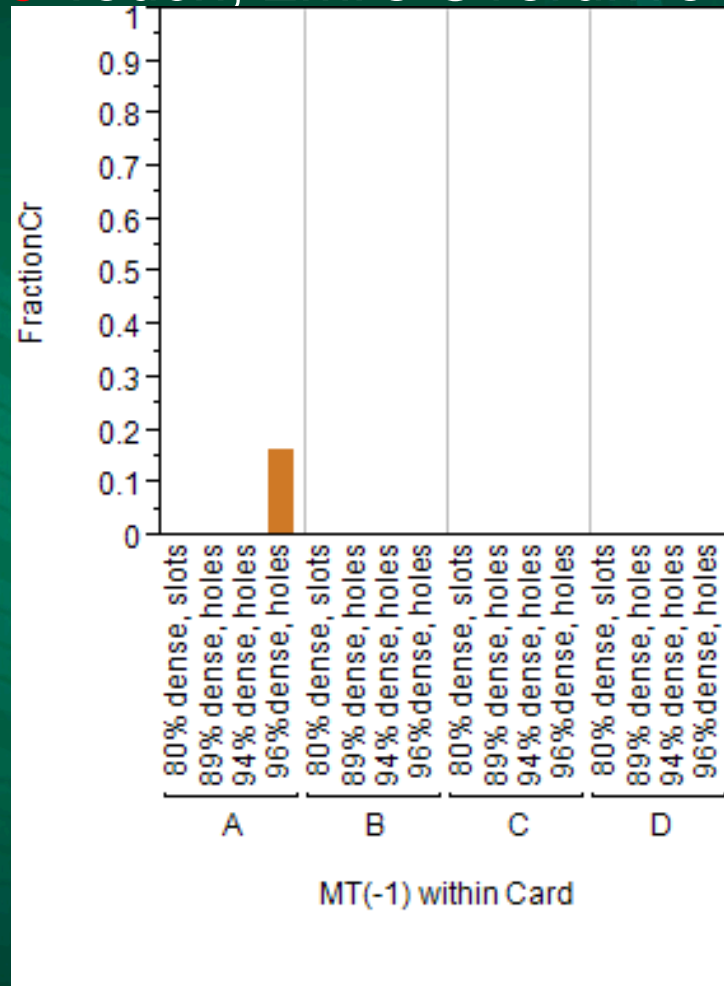


# Probe Card "D"

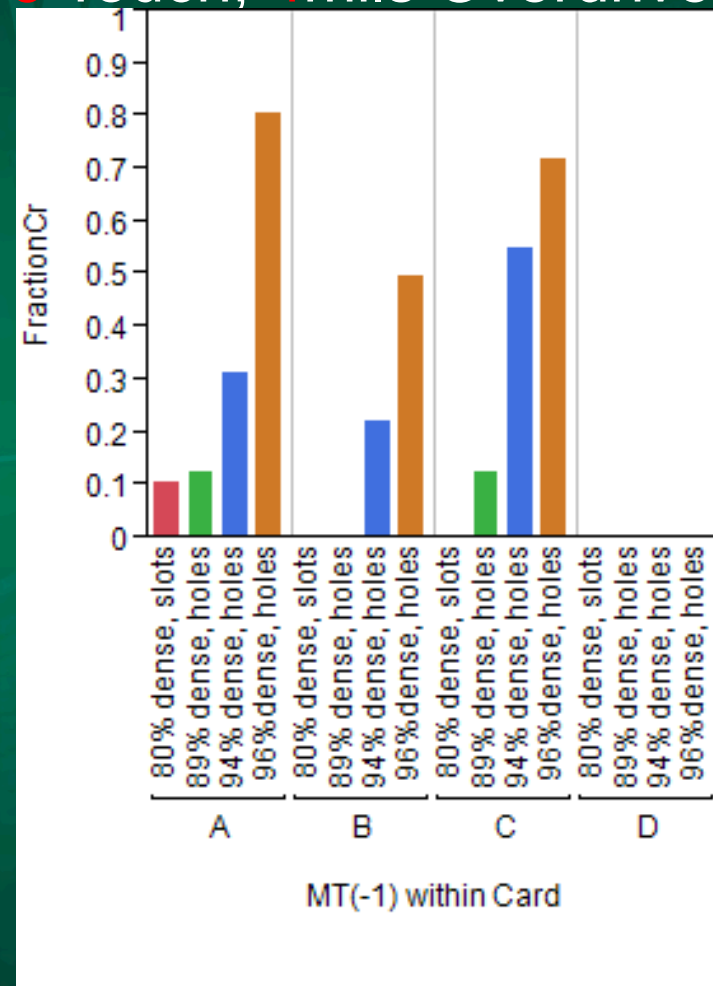


# Fraction Cracked (4 Probe Cards)

6 Touch, 2mils Overdrive



6 Touch, 4mils Overdrive



MT(-1)

80% dense, slots

89% dense, holes

94% dense, holes

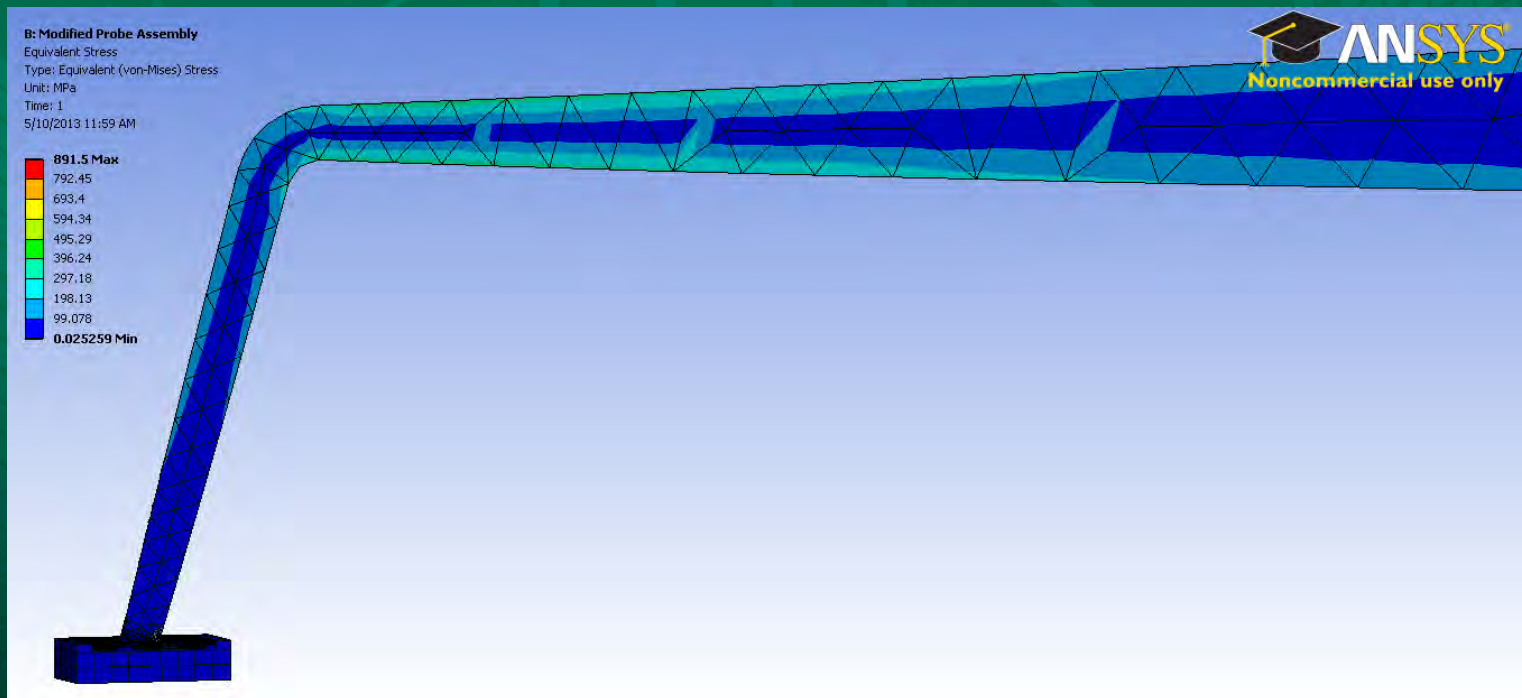
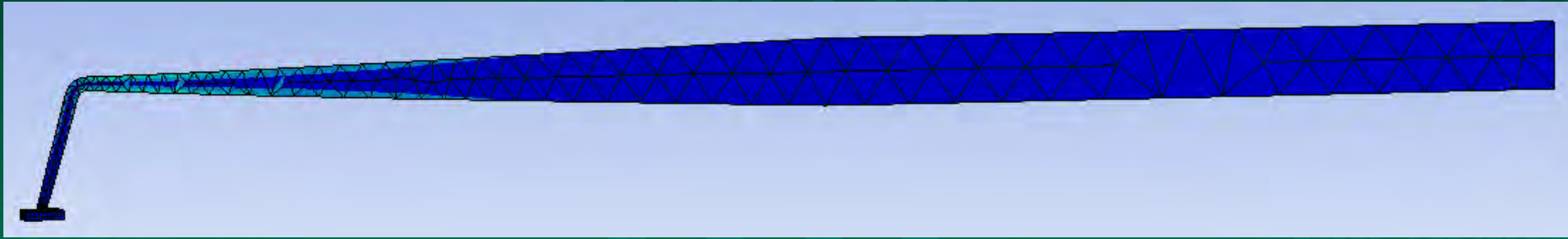
96% dense, holes

# Conclusions for Pad Cracking

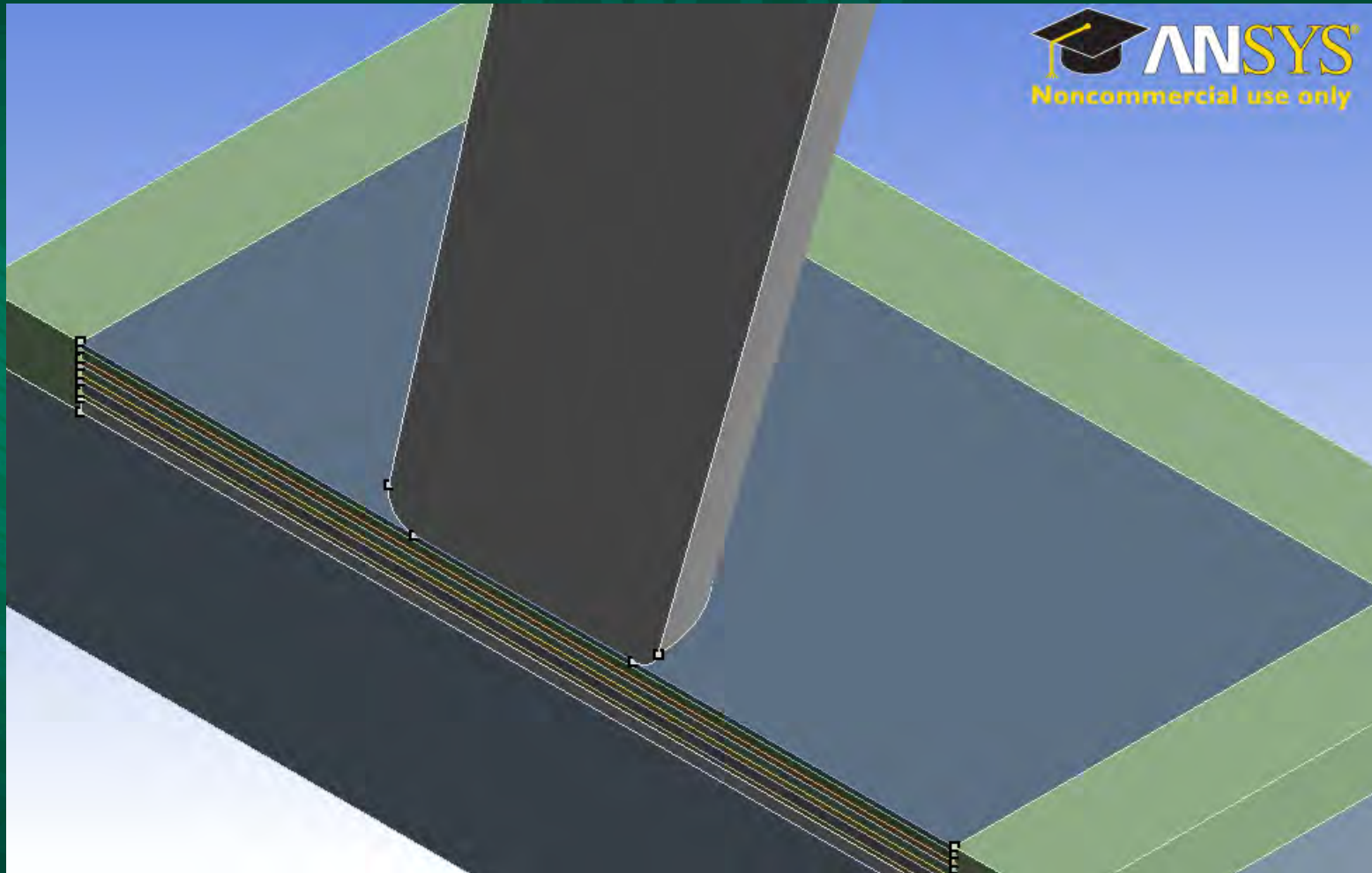
- High Force cantilever probe tips on certain bond pad structures cause cracking
- Cracking increases with overdrive, and high number of touchdowns makes it worse
- Avoid cracking by designing mechanically robust bond pads



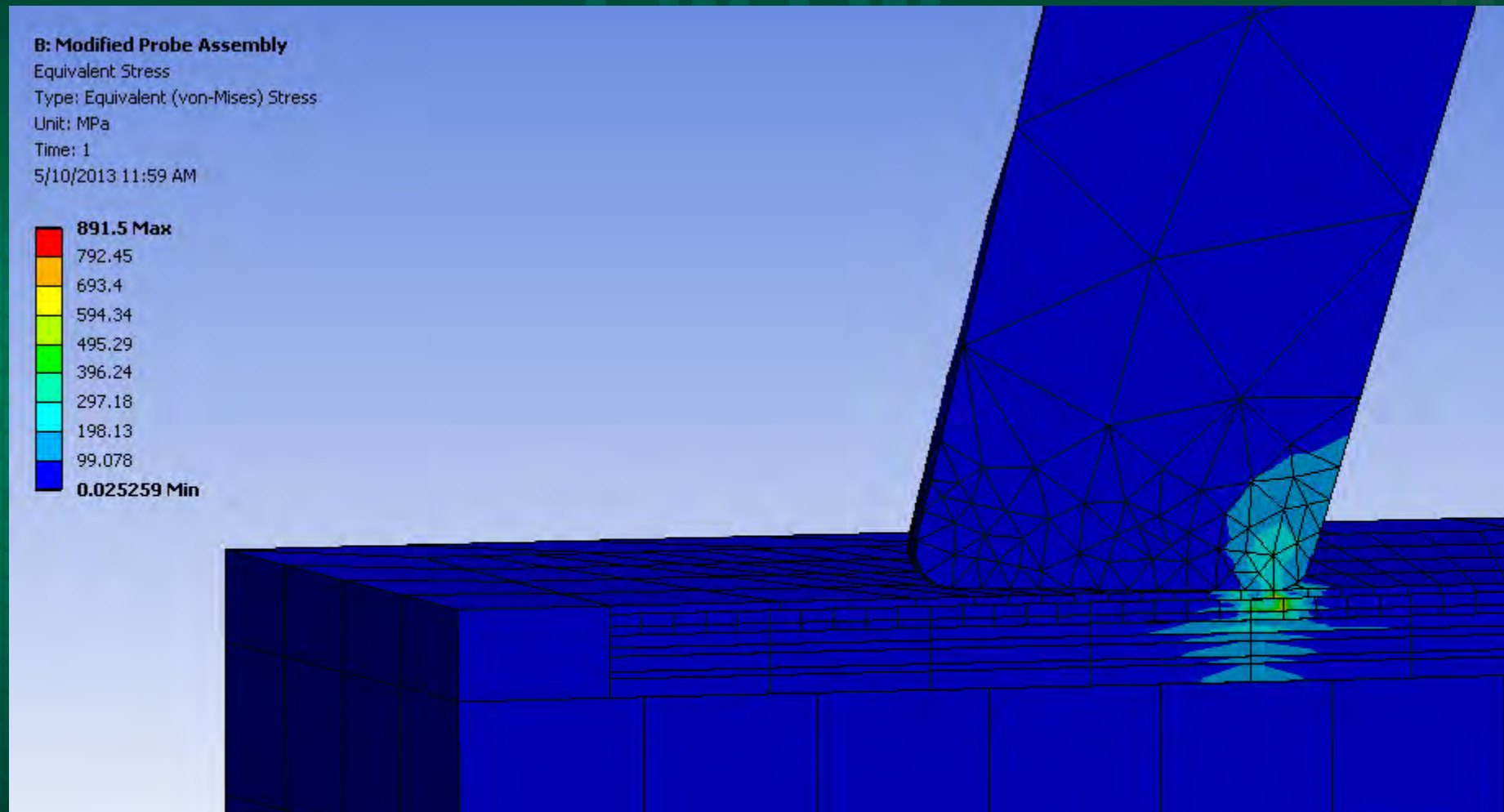
# Cantilever Probe Model



# BYU-Idaho Students: FEM Probing Model

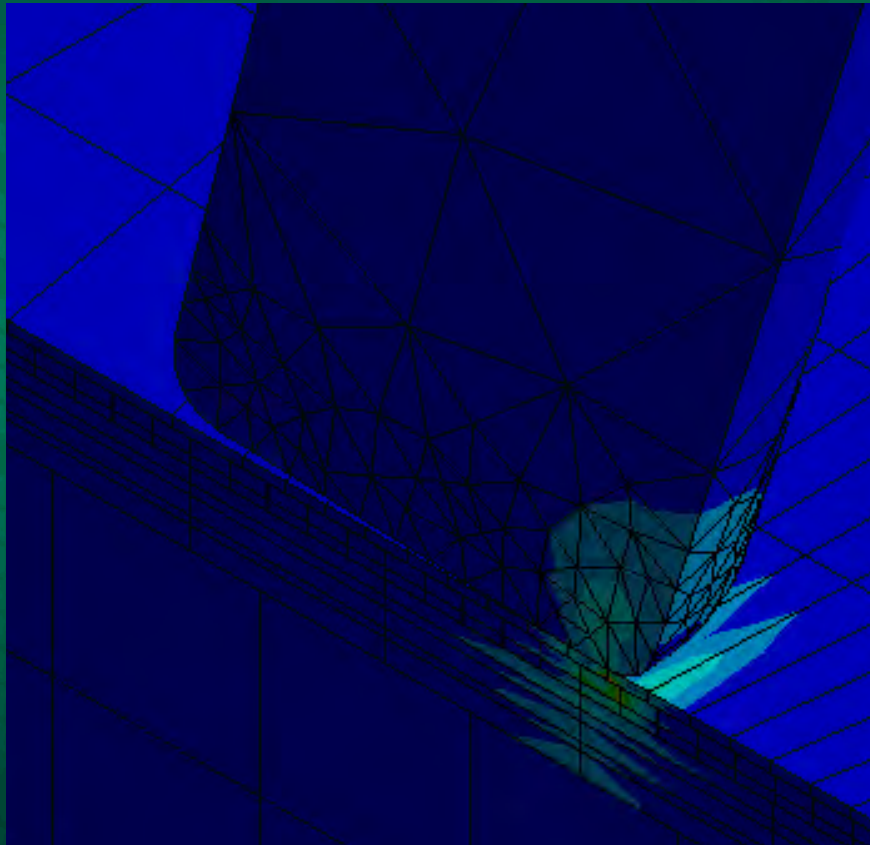


# Probe and Bond Pad Stress Detail

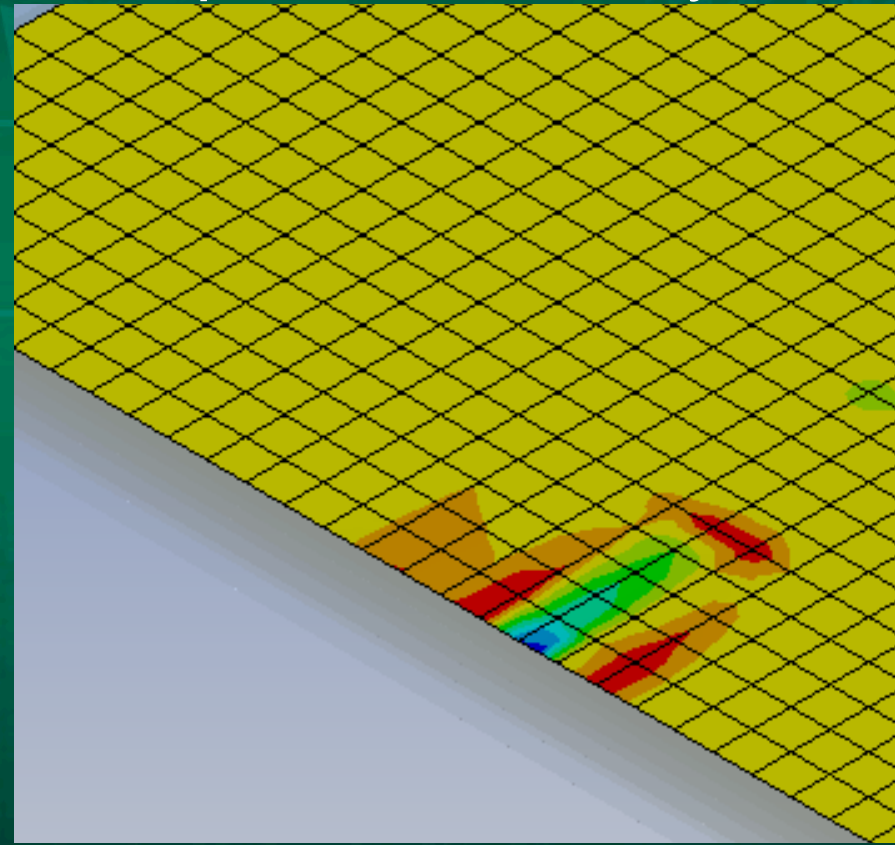


# Basic Stress Analysis

Von Mises Stress in Bond Pad Structure



Max Principal Stress in Top IMD SiO2 Layer





# Example Probe Marks

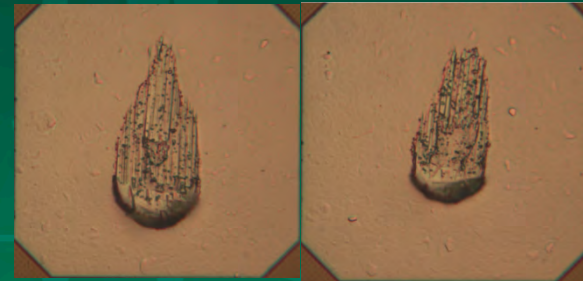
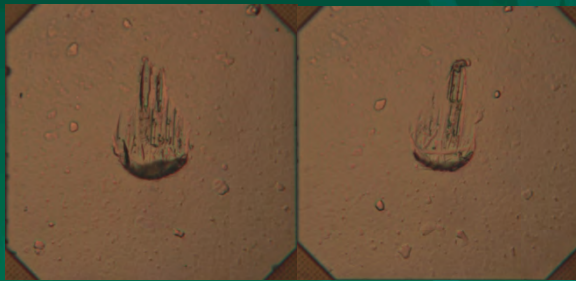
Short Tip

Long Tip

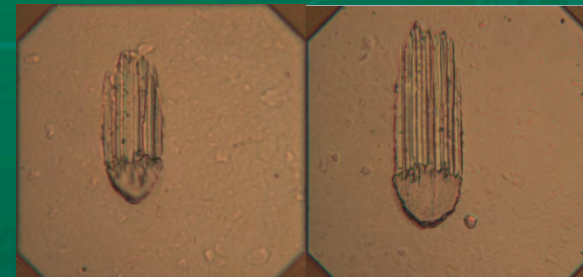
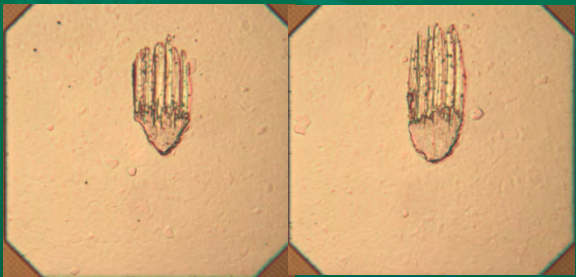
Short Tip

Long Tip

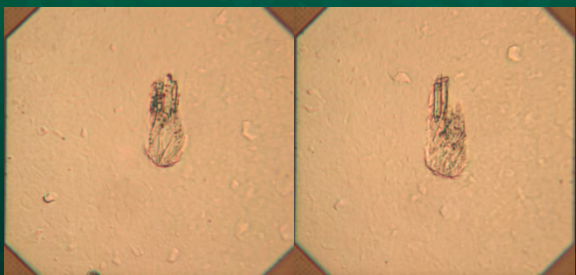
Card  
A



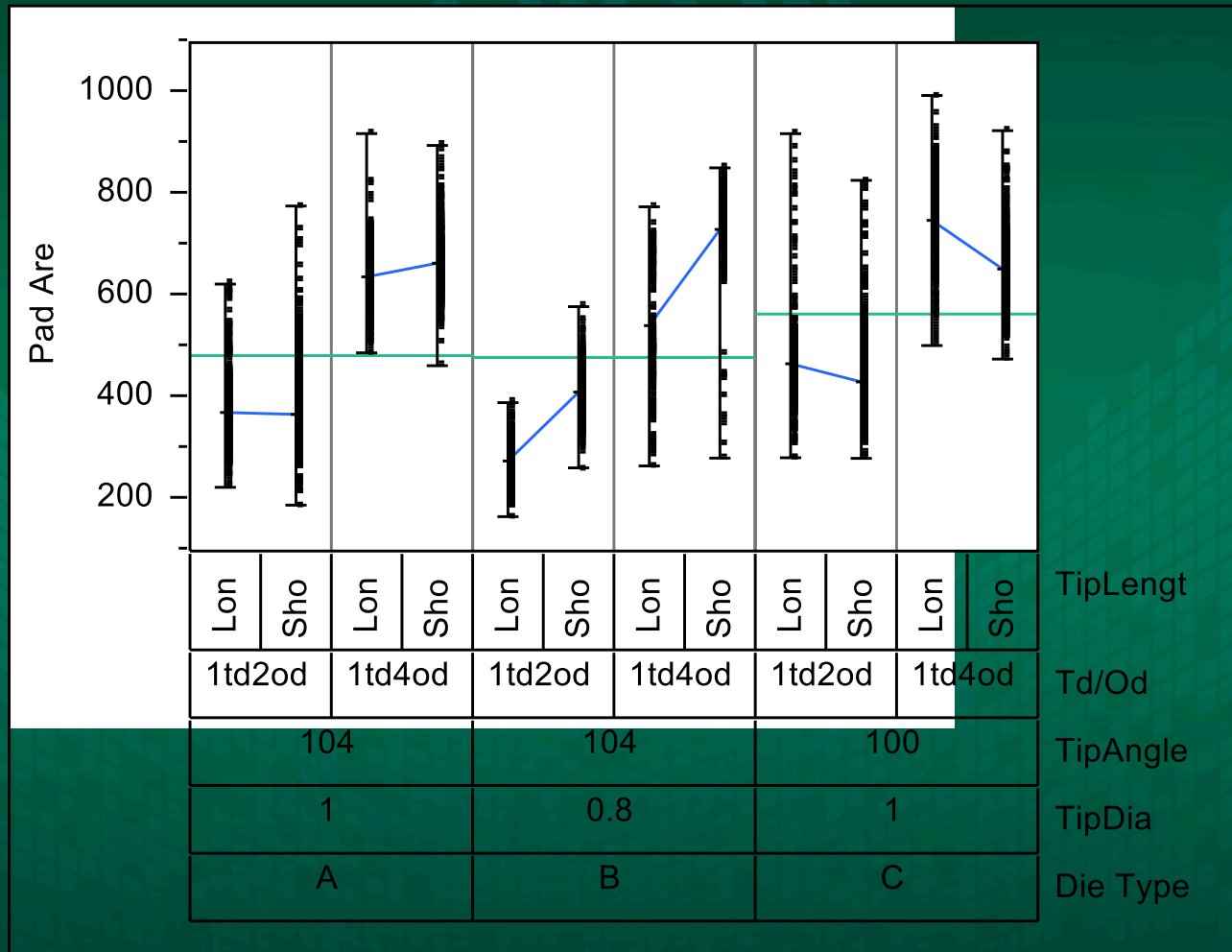
Card  
C



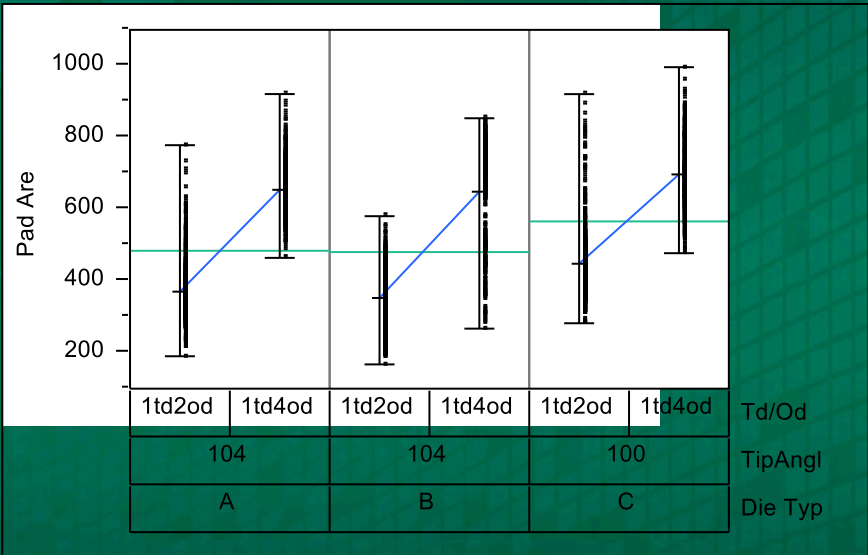
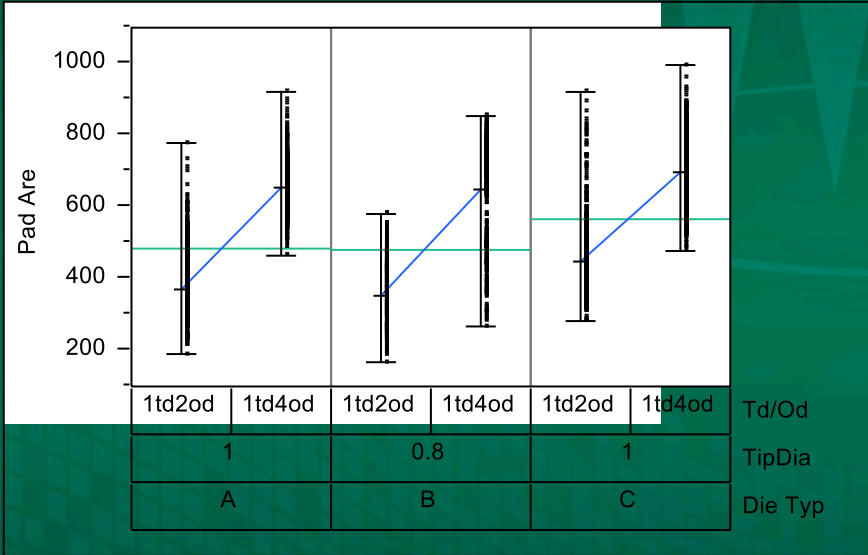
Card  
D



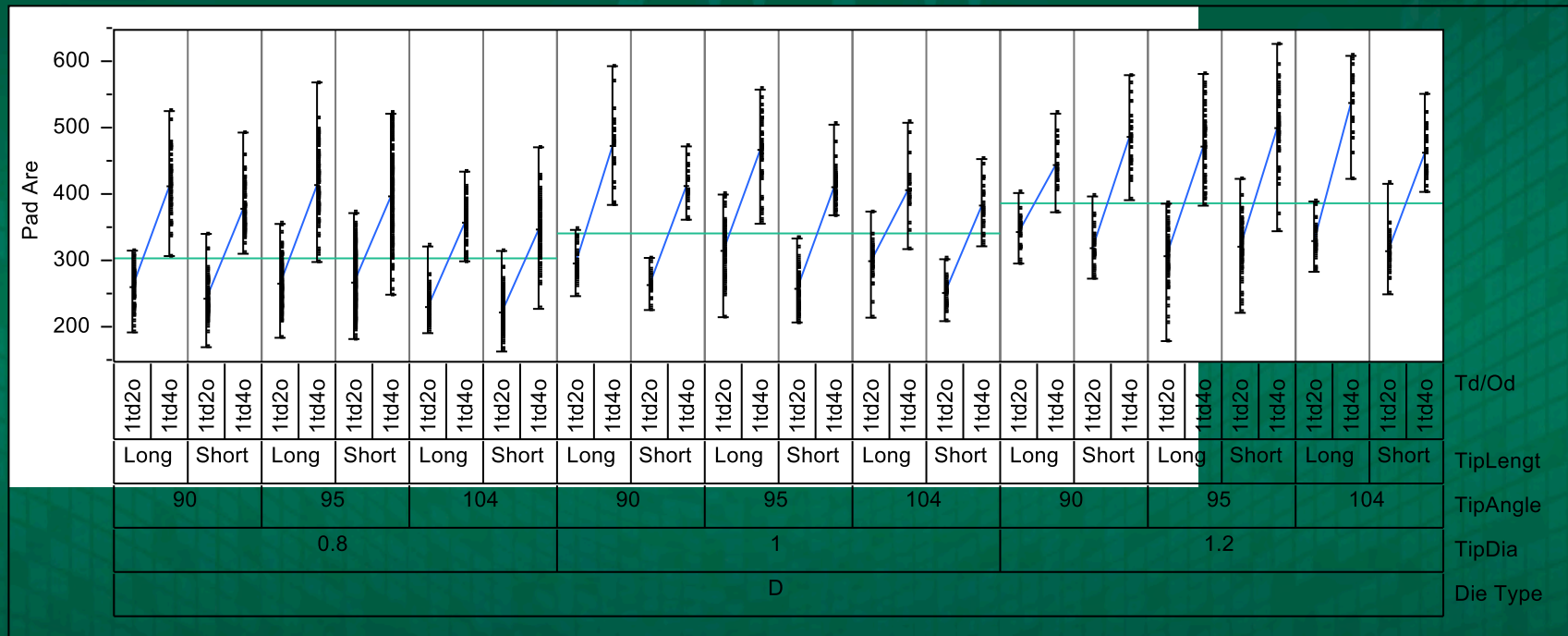
# Probe Mark Area: High Force Probe Tips



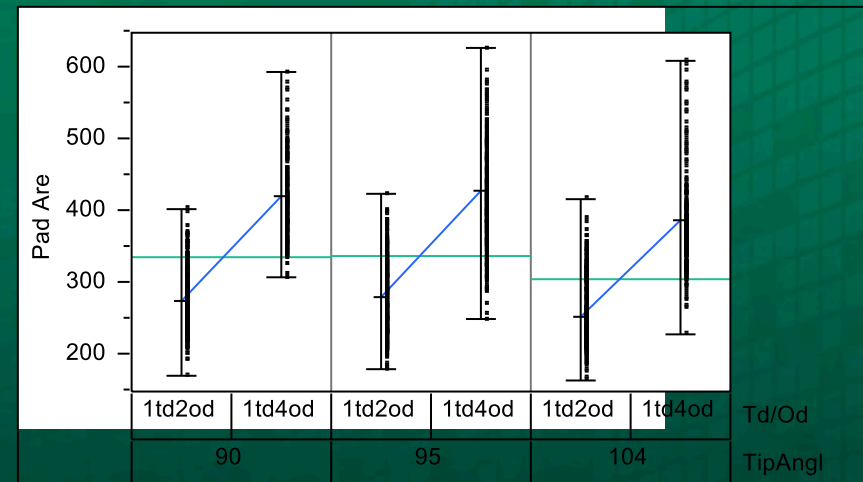
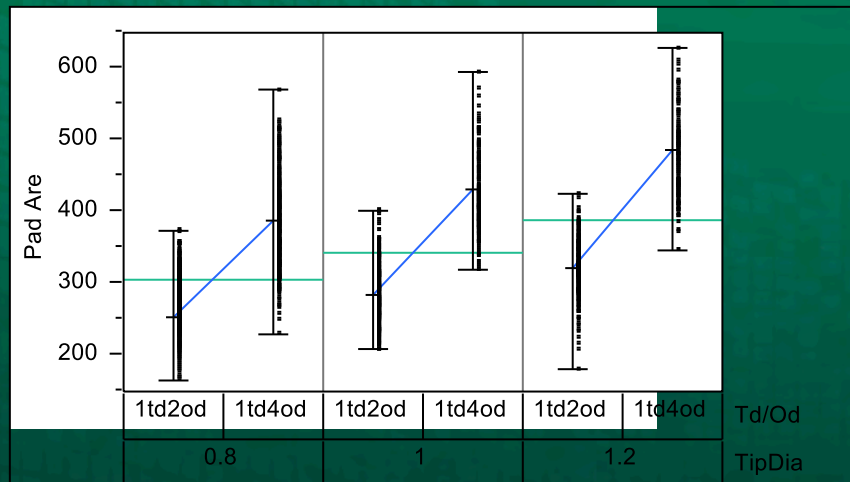
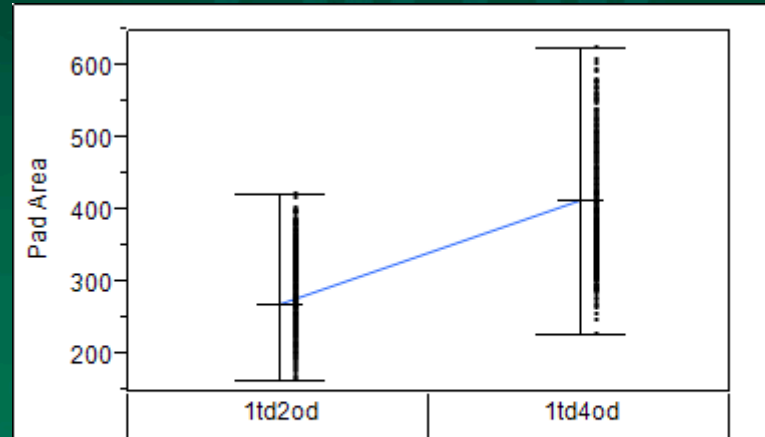
# High Force Probe Tips (cont)



# Probe Mark Area: Probe Card D



# Card D: Overdrive, Tip Dia, Angle



# Conclusions for Probe Mark Area

- **Major factors in large probe mark area:**
  - high force cantilever probes
  - high overdrive
- **Minor factors:**
  - large tip diameter
  - ( $<104^\circ$  tip angle)
- **No effect:**
  - Probe tip length



# Future Work

- Wirebond evaluation and reliability testing on various probe marks:
- Au, Cu, Ag-alloy, ... wire types
- Ball bond, wedge bond
- Finite element modeling

❖ IMAPS International Symposium 2013

❖ IEEE EPTC 2013



# Acknowledgements

- **Supported by ON Semiconductor Quality & Reliability Management**
- **Significant contributions by ON Semiconductor personnel in Pocatello, Idaho:**
  - Pocatello Pilot Line
  - Materials Analysis Lab
- **University Electrical Engineering Departments:**
  - Idaho State University
  - Brigham Young University Idaho

